AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A semiconductor device comprising:

a) a semiconductor layer that is provided over ~~a~~ an insulator layer ~~of electrically insulating material~~having lower thermal conductivity than the semiconductor layer;

b) a plurality of bipolar transistors that are provided on the semiconductor layer such that collectors, emitters and bases of the bipolar transistors are respectively connected in parallel with each other; and

c) an isolation that is provided over a main surface of the semiconductor layer to reach the insulator layer; ~~of electrically insulating material, and provided such that the isolation surrounds a group of or the whole of the plurality of bipolar transistors, such that~~

wherein at least a portion of the plurality of bipolar transistors are surrounded by the insulator layer and the isolation, and

wherein the surrounded transistors operate substantially uniformly as constituent elements of a unit transistor.

2. (Previously Presented) The semiconductor device according to claim 1, wherein

resistors are electrically connected to the emitters of the plurality of bipolar transistors, respectively.

3. (Original) The semiconductor device according to claim 2, wherein

each resistor is comprised of polycrystalline silicon.

4. (Previously Presented) The semiconductor device according to claim 1, wherein

a distance between a contact hole for a base and a contact hole for a collector of mutually adjacent bipolar transistors is a minimum distance between the transistors.

5. (Previously Presented) The semiconductor device according to claim 1, wherein

a distance between a contact hole for a base and a contact hole for a collector of mutually adjacent bipolar transistors is 1 μm or more.

6. (Currently Amended) A semiconductor device comprising:

a) a semiconductor layer that is provided over ~~a~~ an insulator layer ~~of electrically insulating material~~having lower thermal conductivity than the semiconductor layer;

b) a plurality of bipolar transistors that are provided on the semiconductor layer such that collectors, emitters and bases of the bipolar transistors are respectively connected in parallel with each other;

c) resistors which are electrically connected to corresponding ones of the plurality of bipolar transistors; and

d) an isolation that is provided over the main surface of the semiconductor layer to reach the insulator layer; ~~of electrically insulating material, and provided such that the isolation surrounds a group of or the whole of the plurality of bipolar transistors, such that~~

wherein at least a portion of the plurality of bipolar transistors are surrounded by the insulator layer and the isolation, and

wherein the surrounded transistors operate substantially uniformly as constituent elements of a unit transistor.

7. (Original) The semiconductor device according to claim 6, wherein

each resistor is comprised of polycrystalline silicon.

8. (Previously Presented) The semiconductor device according to claim 6, wherein

a distance between a contact hole for a base and a contact hole for a collector of mutually adjacent bipolar transistors is a minimum distance between the transistors.

9. (Previously Presented) The semiconductor device according to claim 6, wherein

a distance between a contact hole for a base and a contact hole for a collector of mutually adjacent bipolar transistors is 1 μm or more.

10. (Currently Amended) A semiconductor device comprising:

a) a semiconductor layer that is provided over ~~a~~ an insulator layer ~~of electrically insulating material~~having lower thermal conductivity than the semiconductor layer;

b) a plurality of first bipolar transistors that are provided in a first region over a portion of the

semiconductor layer such that collectors of the first bipolar transistors are connected in parallel with each other, emitters of the first bipolar transistors are connected in parallel with each other, and bases of the first bipolar transistors are connected in parallel with each other;

c) a first isolation provided ~~in~~ over the main surface of the semiconductor layer to reach the insulator layer; ~~of electrically insulating material, and provided such that the isolation surrounds a group of or the whole of the plurality of first bipolar transistors in the first region, such that the surrounded first bipolar transistors operate substantially uniformly as constituent elements of a first unit transistor;~~

d) a plurality of second bipolar transistors that are provided in a second region over a portion of the semiconductor layer such that collectors of the second bipolar transistors are connected in parallel with each other, emitters of the second bipolar transistors are connected in parallel with each other, and bases of the second bipolar transistors are connected in parallel with each other; and

e) a second isolation that is provided ~~in~~ over the main surface of the semiconductor layer to reach the insulator

layer; ~~of electrically insulating material, and provided such that the isolation surrounds each of the plurality of the second bipolar transistors in the second region, such that~~

wherein at least a portion of the plurality of first bipolar transistors is surrounded by the insulator layer and the first isolation in the first region,

wherein each of the plurality of second bipolar transistors is surrounded by the insulator layer and the second isolation in the second region,

wherein the surrounded first bipolar transistors operate substantially uniformly as constituent elements of a first unit transistor, and

wherein the surrounded second bipolar transistors operate substantially uniformly as constituent elements of a second unit transistor.

11. (Previously Presented) The semiconductor device according to claim 10, wherein

resistors are electrically connected to the emitters of the plurality of the first and second bipolar transistors, respectively.

12. (Original) The semiconductor device according to claim 11, wherein

each resistor is comprised of polycrystalline silicon.

13. (Previously Presented) The semiconductor device according to claim 10, wherein

a distance between a contact hole for a base and a contact hole for a collector of mutually adjacent first bipolar transistors is a minimum distance between the transistors.

14. (Previously Presented) The semiconductor device according to claim 10, wherein

a distance between a contact hole for a base and a contact hole for a collector of mutually adjacent bipolar transistors is 1 μm or more.

15. (Previously Presented) The semiconductor device according to claim 10, wherein

a distance between a contact hole for a base and a contact hole for a collector of mutually adjacent first bipolar transistors is equal to a distance between a contact hole for a base and a contact hole for a collector of mutually adjacent second bipolar transistors.

16. (Original) The semiconductor device according to claim 10, wherein

an optimum current value of the first bipolar transistor is larger than an optimum current value of the second bipolar transistor.

17. (Original) The semiconductor device according to claim 16, wherein

a permissible maximum current value of the first bipolar transistor is larger than a permissible maximum current value of the second bipolar transistor by 1.5 times or more.

18. (Original) The semiconductor device according to claim 10, wherein

the first bipolar transistor constitutes a circuit that requires a heat radiation characteristic that is larger than a heat radiation characteristic of the second bipolar transistor, and the second bipolar transistor constitutes a circuit that requires a higher speed than that of the first bipolar transistor.